





BAT54WS SURFACE MOUNT SCHOTTKY BARRIER DIODE



Features

- Low Turn-on Voltage
- Fast Switching
- PN Junction Guard Ring Transient and ESD Protection
- Designed for Surface Mount Application
- Plastic Material —UL Recognition Flammability Classification 94V-O
- Green Products in Compliance with the ROHS Directive
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Schematic & Pin Configuration



Mechanical Characteristics

Case: SOD-323, Molded plastic

Terminals: Plated Leads Solderable per MIL-STD-202,
No. 1000

Method 208

Polarity: Cathode BandWeight: 0.04 grams(approx)

Maximum Ratings @T_A=25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	V
Forward Continuous Current	I _{FM}	200	mA
Repetitive Peak Forward Current	I _{FRM}	300	mA
Non-Repetitive Peak Forward Surge Current @t<1s	I _{FSM}	600	mA
Power Dissipation	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C





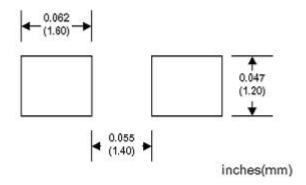


Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristics	Symbol	Condition	Min.	Max.	Units
Reverse Breakdown Voltage*	V_{BR}	@ I _{BS} =100uA	30	-	V
Forward Voltage Drop*	V _{F1}	@ 1.0mA, Pulse, T _J = 25 °C	-	0.32	V
		@ 100mA, Pulse, T _J = 25 °C	-	1	
Reverse Current*	I _{R1}	@V _R = 25V, Pulse, T _J = 25 °C	-	2	μA
Capacitance between terminals	Ст	@V _R = 0 V, Tc=25, f _{SIG} = 1MHz	-	10	pF
Reverse Recovery Time	t _{rr}	I_F =10mA I_R = 10mA		5	no
		$T_J = 25 ^{\circ}\text{C} \text{I}_{\text{rr}} = 1 \text{mA} \text{R}_L = 100 \Omega$	_	5	ns

 $^{^{\}star}$ Pulse width < 300 μ s, duty cycle < 2%

RECOMMENDED FOOTPRINT







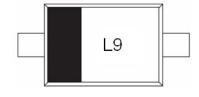


Ordering Information

Device	Package Shipping	
BAT54WS	SOD-323 (Pb-Free)	3000pcs / reel

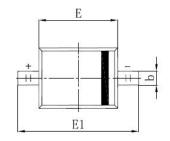
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

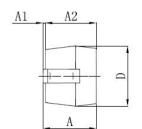
Marking Diagram

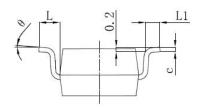


L9 = Marking Code

Mechanical Dimensions SOD-323

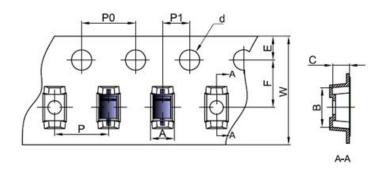






OVMBOL	Millimeters		Inches	
SYMBOL	MIN.	MAX.	MIN.	MAX.
Α	-	1.000	-	0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
С	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
Е	1.600	1.800	0.063	0.071
E1	2.500	2.700	0.098	0.106
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Carrier Tape Specification SOD-323



SYMB	Millimeters		
OL	Min.	Max.	
В	2.85	2.95	
С	1.20	1.30	
d	1.40	1.60	
E	1.65	1.85	
F	3.40	3.60	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
W	7.90	8.30	

- China Germany Korea Singapore United States
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